



STD12N10L

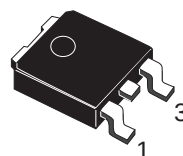
N - CHANNEL 100V - 0.12 Ω - 12A TO-252 LOW THRESHOLD POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD12N10L	100 V	< 0.15 Ω	12 A

- TYPICAL R_{DS(on)} = 0.12 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- HIGH CURRENT CAPABILITY
- 175 °C OPERATING TEMPERATURE
- LOW THRESHOLD DRIVE
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

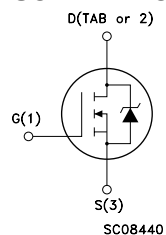
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT(INJECTION, ABS, AIR-BG, LAMPDRIVERS, Etc.)



**DPAK
TO-252**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	100	V
V _{GS}	Gate-source Voltage	± 15	V
I _D	Drain Current (continuous) at T _c = 25 °C	12	A
I _D	Drain Current (continuous) at T _c = 100 °C	8	A
I _{DM} (•)	Drain Current (pulsed)	48	A
P _{tot}	Total Dissipation at T _c = 25 °C	50	W
	Derating Factor	0.33	W/°C
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

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THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	1.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		275	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 15 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 6 A V _{GS} = 5V I _D = 6 A		0.12 0.17	0.15 0.2	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	12			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 6 A	6.5	10		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		800 150 50		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 50\text{ V}$ $I_D = 6\text{ A}$		15		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, see fig. 3)		40		ns
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$ $I_D = 12\text{ A}$ $V_{GS} = 5\text{ V}$		20	30	nC
Q_{gs}	Gate-Source Charge			6		nC
Q_{gd}	Gate-Drain Charge			10		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 80\text{ V}$ $I_D = 12\text{ A}$		12		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$		12		ns
t_c	Cross-over Time	(Inductive Load, see fig. 5)		25		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				12	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				48	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 12\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		145		ns
Q_{rr}	Reverse Recovery Charge			580		μC
I_{RRM}	Reverse Recovery Current			8		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Fig. 2: Unclamped Inductive Waveform

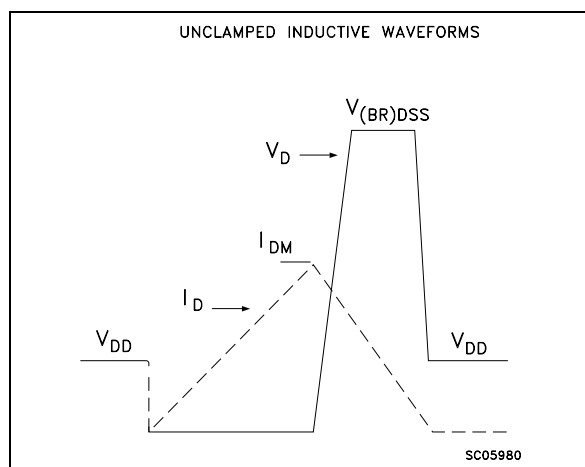
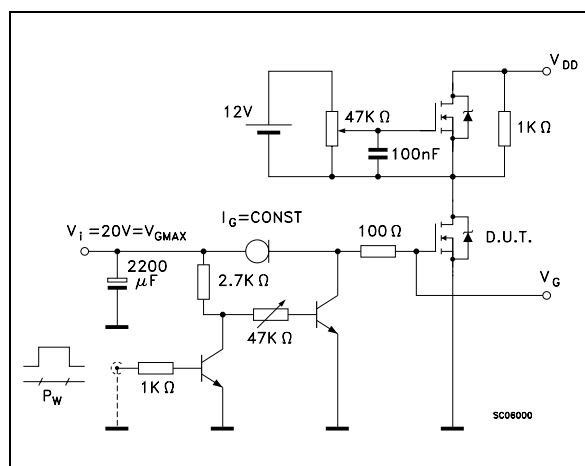
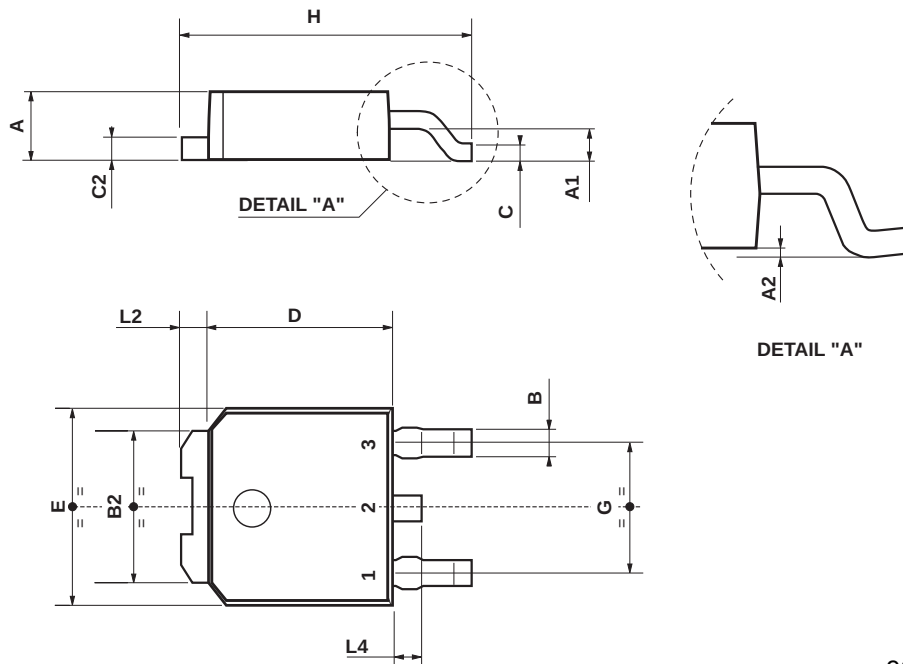


Fig. 4: Gate Charge test Circuit



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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